

isc Triacs

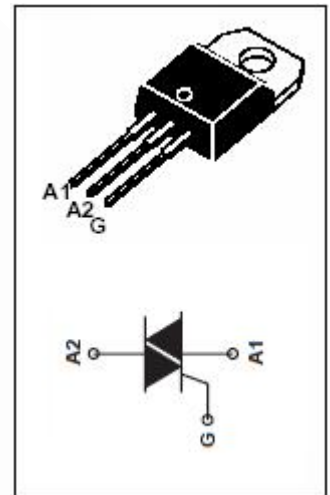
BTB04 T/D/S/A

FEATURES

- With TO-220AB non insulated package
- Suitable for general purpose applications where gate high sensitivity is required. Application on 4Q such as phase control and static switching.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	MIN	UNIT
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_j=95^\circ\text{C}$	4	A
$I_{TSM}$	Non-repetitive peak on-state current $t_p=10\text{ms}$	40	A
$T_j$	Operating junction temperature	110	°C
$T_{stg}$	Storage temperature	-45~150	°C
$R_{th(j-c)}$	Thermal resistance, junction to case	3.2	°C/W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	60	°C/W



SYMBOL	PARAMETER	400T/D/S/A	600T/D/S/A	700T/D/S/A	UNIT
$V_{DRM}$	Repetitive peak off-state voltage	400	600	700	V
$V_{RRM}$	Repetitive peak reverse voltage	400	600	700	V

ELECTRICAL CHARACTERISTICS (Tc=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MAX				UNIT	
$I_{RRM}$	Repetitive peak reverse current	$V_R=V_{RRM}$ , $V_R=V_{RRM}$ , $T_j=110^\circ\text{C}$	0.01 0.75				mA	
$I_{DRM}$	Repetitive peak off-state current	$V_D=V_{DRM}$ , $V_D=V_{DRM}$ , $T_j=110^\circ\text{C}$	0.01 0.75				mA	
$I_{GT}$	Gate trigger current	$V_D=12\text{V}$ ; $R_L=33\ \Omega$	I - II - III	T	D	S	A	mA
				5	5	10	10	
			IV	5	10	10	25	
$I_H$	Holding current	$I_{GT}=0.1\text{A}$ , Gate Open	15	15	25	25	mA	
$V_{GT}$	Gate trigger voltage all quadrant	$V_D=12\text{V}$ ; $R_L=30\ \Omega$	1.5				V	
$V_{TM}$	On-state voltage	$I_T=5\text{A}$	1.65				V	